

INFORMATION DISCLOSURE STATEMENT PTO-1449	Atty. Docket No. 031111	Serial No. New Application
	Applicant(s): Mitsuaki Hori, et al.	
	Filing Date: September 16, 2003	Group Art Unit: Not Yet Assigned

U.S. PATENT DOCUMENTS

Examiner Initial	Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
<u>AS</u>	AA 6,215,146	Umeda et al.	04/10/01			
	AB					
	AC					
	AD					

FOREIGN PATENT DOCUMENTS

	Document No.	Date	Country	Translation (Yes or No)
<u>AS</u>	AE 11-204787	07/30/99	Japan	Yes-Abstract/Discussed in the specification
	AF			
	AG			
	AH			
	AI			

OTHER DOCUMENTS

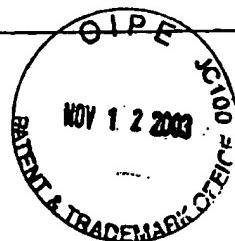
<u> </u>	AJ	
<u> </u>	AK	

Examiner	<u>NY</u>	Date Considered	<u>12/05/04</u>
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INFORMATION DISCLOSURE CITATION PTO-1449	Atty. Docket No. 031111	Serial No. 10/662,384
	Applicant(s): Hori, et al.	
	Filing Date: September 16, 2003	Group Art Unit: Unassigned

U.S. PATENT DOCUMENTS

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<i>AS</i>	A K AL	Chen et al., Downscaling Limit of Equivalent Oxide Thickness in Formation of Ultrathin Gate Dielectric by Thermal-Enhanced Remote Plasma Nitridation, IEEE TRANSACTIONS ON ELECTRON DEVICES, May 2002, Vol. 49, No.5, P.840-845
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Examiner

AS

Date Considered

10/15/04